

Page 12, line 11, after "distance" insert --therebetween--;

line 18, after "portions" insert --of film 12--;

line 27, change "to have a pattern" to --into distinct regions--;

line 28, change "is" to --are-- and then add --of these regions-- at the end of the line; and

line 29, after "10a" insert --(Fig.3D)--.

IN THE CLAIMS:

Kindly amend claim 1 as follows:

1. (Amended) A method for manufacturing a semiconductor device having a buried conductive layer which is connected to one of a source and a drain of a MOS transistor and extends over a gate electrode of said MOS transistor, said method comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a first conductive film as said gate electrode and a second insulating film on said first insulating film, said gate electrode having a width equal to a minimum processing size achievable with a lithographic process technique;

forming a third insulating film on the whole surface of said semiconductor substrate having said first insulating film, said first conductive film and said second insulating film formed thereon;